

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuya SHIMODA et al.

Application No.: U.S. National Stage Application of
PCT/JP99/00864

Filed: October 25, 1999

Docket No.: 104270

For: THREE-DIMENSIONAL DEVICE

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE ABSTRACT:

A memory IC includes a first substrate (substrate on the transfer destination side), and memory cell arrays deposited on the first substrate. The memory cell arrays are deposited from the bottom up by a method for transferring a thin film configuration. The transferring method includes the steps of forming a thin film device layer (memory cell array) on a second substrate with a separable layer therebetween, and irradiating the separable layer with light to cause a separation in the separable layer and/or at an interface so that the thin film device layer on the second substrate is transferred to the first substrate.

IN THE SPECIFICATION:

Page 1, line 1, delete "DESCRIPTION"; and